

Silicon PNP Power Transistors

2SB954 2SB954A

DESCRIPTION

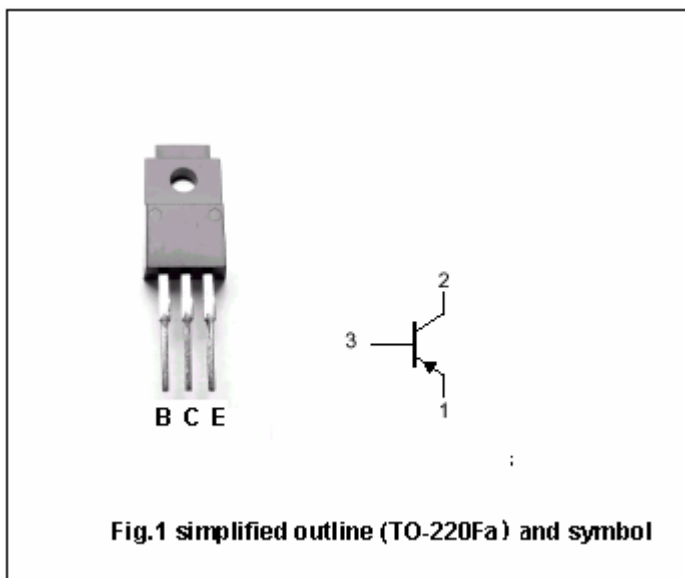
- With TO-220Fa package
- High forward current transfer ratio h_{FE} which has satisfactory linearity
- Low collector saturation voltage

APPLICATIONS

- For power amplification

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base



Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2SB954	-60	V
		2SB954A	-80	
V _{CEO}	Collector-emitter voltage	2SB954	-60	V
		2SB954A	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-1	A
I _{CM}	Collector current-peak		-2	A
P _C	Collector power dissipation	T _a =25□	2	W
		T _C =25□	30	
T _j	Junction temperature		150	□
T _{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter voltage	2SB954	I _C =-30mA ; I _B =0	-60		V
		2SB954A		-80		
V _{CEsat}	Collector-emitter saturation voltage	I _C =-1.0A ; I _B =-0.125A			-1.0	V
V _{BE}	Base-emitter voltage	I _C =-1A ; V _{CE} =-4V			-1.3	V
I _{CEO}	Collector cut-off current	2SB954	V _{CE} =-30V ; I _B =0		-300	μA
		2SB954A		V _{CE} =-60V ; I _B =0		
I _{CES}	Collector cut-off current	2SB954	V _{CE} =-60V ; V _{BE} =0		-200	μA
		2SB954A		V _{CE} =-80V ; V _{BE} =0		
I _{EBO}	Emitter cut-off current	V _{EB} =-5V ; I _C =0			-1	mA
h _{FE-1}	DC current gain	I _C =-0.2A ; V _{CE} =-4V	70		250	
h _{FE-2}	DC current gain	I _C =-1A ; V _{CE} =-4V	15			
f _T	Transition frequency	I _C =-0.2A ; V _{CE} =-5V, f=10MHz		30		MHz
t _{on}	Trun-on time	I _C =-1A ; V _{CC} =-50V I _{B1} =-0.1A, I _{B2} =0.1A		0.5		μs
t _s	Storage time			1.2		μs
t _f	Fall time			0.3		μs

◆ h_{FE-1} Classifications

Q	P
70-150	120-250

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PACKAGE OUTLINE

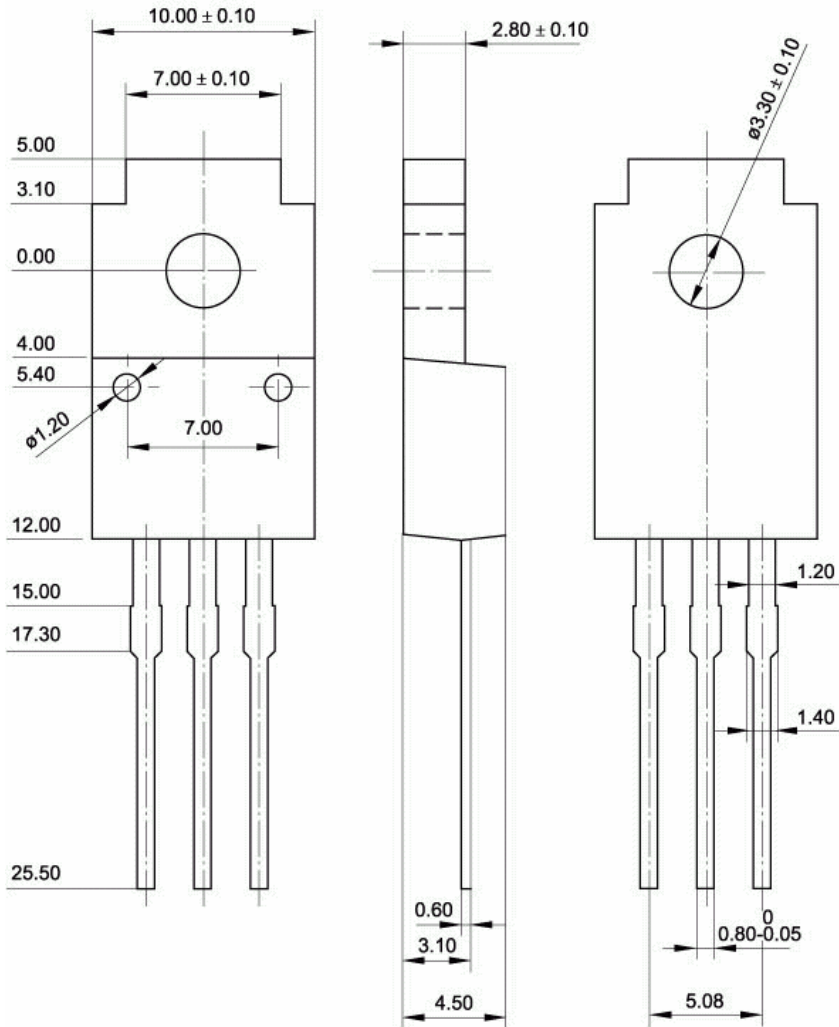


Fig.2 Outline dimensions (unindicated tolerance: ± 0.15 mm)

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